

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Tatsuya SHIMODA et al.

Application No.: U.S. National Stage Application of  
PCT/JP99/00864

Filed: October 25, 1999

Docket No.: 104270

For: THREE-DIMENSIONAL DEVICE

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE ABSTRACT:

01  
--A memory IC includes a first substrate (substrate on the transfer destination side),  
and memory cell arrays deposited on the first substrate. The memory cell arrays are  
deposited from the bottom up by a method for transferring a thin film configuration. The  
transferring method includes the steps of forming a thin film device layer (memory cell array)  
on a second substrate with a separable layer therebetween, and irradiating the separable layer  
with light to cause a separation in the separable layer and/or at an interface so that the thin  
film device layer on the second substrate is transferred to the first substrate.

IN THE SPECIFICATION:

Page 1, line 1, delete "DESCRIPTION"; and